



2-Mbit (128K x 16) Static RAM

Features

■ Very high speed: 45 ns

■ Temperature ranges

☐ Industrial: −40°C to +85°C
☐ Automotive-A: −40°C to +85°C
☐ Automotive-E: −40°C to +125°C
■ Wide voltage range: 2.20V-3.60V

■ Pin compatible with CY62136V, CY62136CV30/CV33, and

CY62136EV30

■ Ultra low standby power

□ Typical standby current: 1μA

Maximum standby current: 5 μA (Industrial)

■ Ultra low active power

Typical active current: 1.6 mA at f = 1 MHz (45 ns speed)

■ Easy memory expansion with CE and OE features

■ Automatic power down when deselected

■ CMOS for optimum speed and power

■ Available in Pb-free 48-ball VFBGA and 44-pin TSOP II packages

Functional Description

The CY62136FV30 is a high performance CMOS static RAM organized as 128K words by 16 bits. This device features advanced circuit design to provide ultra low active current. This is ideal for providing More Battery Life $^{\text{TM}}$ (MoBL $^{\text{®}}$) in portable applications such as cellular telephones. The device also has an

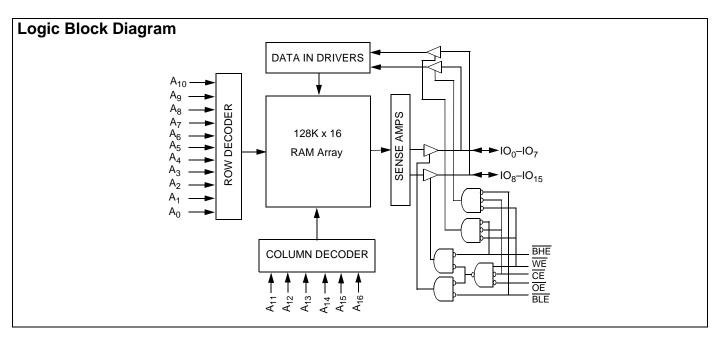
automatic power down feature that significantly reduces power consumption by 90% when addresses are not toggling. Placing the device into standby mode reduces power consumption by more than 99% when deselected ($\overline{\text{CE}}$ HIGH). The input and output pins (IO $_0$ through IO $_{15}$) are placed in a high impedance state when:

- Deselected (CE HIGH)
- Outputs are disabled (OE HIGH)
- Both Byte High Enable and Byte Low Enable are disabled (BHE, BLE HIGH)
- Write operation is active (CE LOW and WE LOW)

Write to the device by taking Chip Enable (\overline{CE}) and Write Enable (\overline{WE}) inputs LOW. If Byte Low Enable (\overline{BLE}) is LOW, then data from IO pins $(IO_0$ through $IO_7)$ is written into the location specified on the address pins $(A_0$ through $A_{16})$. If Byte High Enable (\overline{BHE}) is LOW, then data from IO pins $(IO_8$ through $IO_{15})$ is written into the location specified on the address pins $(A_0$ through $A_{16})$.

Read from the device by taking Chip Enable (CE) and Output Enable ($\overline{\text{OE}}$) LOW while forcing the Write Enable (WE) HIGH. If Byte Low Enable (BLE) is LOW, then data from the memory location specified by the address pins appears on IO $_0$ to IO $_7$. If Byte High Enable (BHE) is LOW, then data from memory appears on IO $_8$ to IO $_{15}$. See the "Truth Table" on page 9 for a complete description of read and write modes.

For best practice recommendations, refer to the Cypress application note AN1064, SRAM System Guidelines.



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Product Portfolio

							Power Dissipation				n		
Product	Pango	V _C	_C Range	Range (V) Speed Operating I _{CC} (mA) Standby I _{SB}		Operating I _{CC} (mA) Stand		oy I _{SB2}					
Product	Range				(ns)	f = 1	MHz	$f = f_{max}$ (mÅ		Á)			
		Min	Typ [1]	Max		Typ [1]	Max	Typ [1]	Max	Typ [1]	Max		
CY62136FV30LL	Ind'I/Auto-A	2.2	3.0	3.6	45	1.6	2.5	13	18	1	5		
	Auto-E	2.2	3.0	3.6	55	2	3	15	25	1	20		

Pin Configuration

Figure 1. 48-Ball VFBGA Pinout [2, 3]

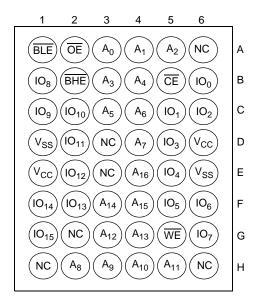
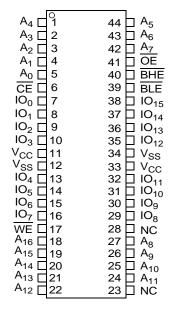


Figure 2. 44-Pin TSOP II [2]



Notes

- 1. Typical values are included for reference only and are not guaranteed or tested. Typical values are measured at $V_{CC} = V_{CC(typ)}$, $T_A = 25^{\circ}C$.
- NC pins are not connected on the die.
 Pins D3, H1, G2, and H6 in the VFBGA package are address expansion pins for 4 Mb, 8 Mb, 16 Mb, and 32 Mb, respectively.



Maximum Ratings

Exceeding the maximum ratings may impair the useful life of the device. These user guidelines are not tested.

Storage Temperature-65°C to + 150°C

Ambient Temperature with

Power Applied55°C to + 125°C

Supply Voltage to Ground

Potential-0.3V to 3.9V (V_{CC(max)} + 0.3V)

DC Voltage Applied to Outputs

in High Z State $^{[4, 5]}$-0.3V to 3.9V ($V_{CC(max)}$ + 0.3V)

DC Input Voltage $^{[4, 5]}$ 0.3V to 3.9V ($V_{CC(max)}$ + 0.3	V)
Output Current into Outputs (LOW)20 m	ìΑ
Static Discharge Voltage > 2001 (MIL-STD-883, Method 3015)	IV
Latch Up Current> 200 m	ìΑ

Operating Range

Device	Range	Ambient Temperature	V _{CC} [6]
CY62136FV30LL	Ind'l/Auto-A	-40°C to +85°C	2.2V to 3.6V
	Auto-E	–40°C to +125°C	

Electrical Characteristics

Over the Operating Range

				-45 (Ind'I/Auto-A)		•	·55 (Au	ito-E)		
Parameter	Description	Test Co	onditions	Min	Typ ^[1]	Max	Min	Typ ^[1]	Max	Unit
V _{OH}	Output HIGH Voltage	$2.2 \le V_{CC} \le 2.7$	$I_{OH} = -0.1 \text{ mA}$	2.0			2.0			V
		$2.7 \le V_{CC} \le 3.6$	$I_{OH} = -1.0 \text{ mA}$	2.4			2.4			V
V _{OL}	Output LOW Voltage	2.2 ≤ V _{CC} ≤ 2.7	I _{OL} = 0.1 mA			0.4			0.4	V
		$2.7 \le V_{CC} \le 3.6$	I _{OL} = 2.1mA			0.4			0.4	V
V _{IH}	Input HIGH Voltage	$2.2 \le V_{CC} \le 2.7$		1.8		V _{CC} + 0.3	1.8		V _{CC} + 0.3	V
		$2.7 \le V_{CC} \le 3.6$		2.2		V _{CC} + 0.3	2.2		V _{CC} + 0.3	V
V _{IL}	Input LOW Voltage	$2.2 \le V_{CC} \le 2.7$		-0.3		0.6	-0.3		0.6	V
		$2.7 \le V_{CC} \le 3.6$	$7.7 \le V_{CC} \le 3.6$			0.8	-0.3		0.8	V
I _{IX}	Input Leakage Current	$GND \le V_1 \le V_{CC}$	$SND \le V_1 \le V_{CC}$			+1	-4		+4	μΑ
I _{OZ}	Output Leakage Current	$GND \le V_O \le V_{CC}$, Ou	tput Disabled	-1		+1	-4		+4	μА
I _{CC}	V _{CC} Operating Supply	$f = f_{max} = 1/t_{RC}$	$V_{CC} = V_{CCmax}$		13	18		15	25	mA
	Current	f = 1 MHz	I _{OUT} = 0 mA CMOS Levels		1.6	2.5		2	3	
I _{SB1}		f = f _{max} (Address an	$\overrightarrow{CE} \ge V_{CC} - 0.2V$, $\overrightarrow{V}_{IN} \ge V_{CC} - 0.2V$, $\overrightarrow{V}_{IN} \le 0.2V$, $\overrightarrow{=} f_{max}$ (Address and Data Only), $\overrightarrow{=} 0$ (OE, WE, BHE, and BLE), $\overrightarrow{V}_{CC} = 3.60V$		1	5		1	20	μА
I _{SB2} ^[7]	Automatic CE Power Down Current — CMOS Inputs	$\overline{\text{CE}} \ge \text{V}_{\text{CC}} - 0.2\text{V},$ $\text{V}_{\text{IN}} \ge \text{V}_{\text{CC}} - 0.2\text{V} \text{ or }$ $\text{f} = 0, \text{V}_{\text{CC}} = 3.60\text{V}$	$EE \ge V_{CC} - 0.2V,$ $V_{IN} \ge V_{CC} - 0.2V \text{ or } V_{IN} \le 0.2V,$		1	5		1	20	μА

Capacitance

Tested initially and after any design or process changes that may affect these parameters.

Parameter	Description	Test Conditions	Max	Unit
C _{IN}	Input Capacitance	$T_A = 25^{\circ}C, f = 1 \text{ MHz},$	10	pF
C _{OUT}	Output Capacitance	$V_{CC} = V_{CC(typ)}$	10	pF

- 4. $V_{IL(min)} = -2.0V$ for pulse durations less than 20 ns.

- V_{IL(min)} = -2.0 V ior pulse durations less than 20 ns.
 V_{IH(max)}=V_{CC}+0.75V for pulse durations less than 20 ns.
 Full device AC operation assumes a minimum of 100 μs ramp time from 0 to V_{CC}(min) and 200 μs wait time after V_{CC} stabilization.
 Only chip enable (ĈE) and byte enables (BHE and BLE) are tied to CMOS levels to meet the I_{SB2} / I_{CCDR} specification. Other inputs can be left floating.

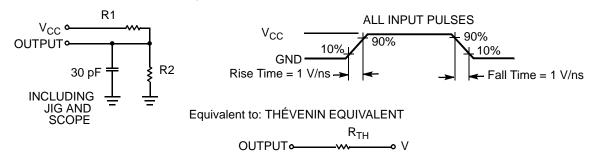


Thermal Resistance

Tested initially and after any design or process changes that may affect these parameters.

Parameter	Description	Test Conditions	VFBGA	TSOP II	Unit
Θ_{JA}		Still air, soldered on a 3 x 4.5 inch, two layer printed circuit board	75	77	°C/W
ΘJC	Thermal Resistance (Junction to Case)		10	13	°C/W

Figure 3. AC Test Loads and Waveforms



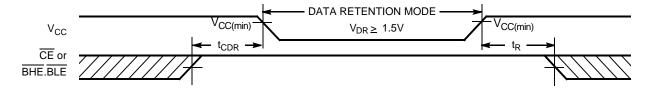
Parameters	2.5V (2.2V to 2.7V)	3.0V (2.7V to 3.6V)	Unit
R1	16667	1103	Ω
R2	15385	1554	Ω
R _{TH}	8000	645	Ω
V _{TH}	1.20	1.75	V

Data Retention Characteristics

Over the Operating Range

Parameter	Description	Description Conditions				Max	Unit
V_{DR}	V _{CC} for Data Retention			1.5			V
I _{CCDR} ^[7]	Data Retention Current	$V_{CC} = 1.5V, \overline{CE} \ge V_{CC} - 0.2V,$ $V_{IN} \ge V_{CC} - 0.2V \text{ or } V_{IN} \le 0.2V$	Ind'l/Auto-A			4	μΑ
		$V_{IN} \ge V_{CC} - 0.2V \text{ or } V_{IN} \le 0.2V$	Auto-E			12	
t _{CDR} [8]	Chip Deselect to Data Retention Time			0			ns
t _R ^[9]	Operation Recovery Time			t _{RC}			ns

Figure 4. Data Retention Waveform [10]



- 8. Tested initially and after any design or process changes that may affect these parameters.

 9. <u>Full device</u> operation requires <u>line</u>ar V_{CC} ramp from V_{DR} to V_{CC(min)} ≥ 100 μs or stable at V_{CC(min)} ≥ 100 μs.

 10. BHE.BLE is the AND of both BHE and BLE. Deselect the chip by either disabling chip enable signals or by disabling both BHE and BLE.



Switching Characteristics

Over the Operating Range [11, 12]

	2	-45 (Ind	I/Auto-A)	-55 (A	uto-E)	11.24
Parameter	Description	Min	Max	Min	Max	Unit
Read Cycle						
t _{RC}	Read Cycle Time	45		55		ns
t _{AA}	Address to Data Valid		45		55	ns
t _{OHA}	Data Hold from Address Change	10		10		ns
t _{ACE}	CE LOW to Data Valid		45		55	ns
t _{DOE}	OE LOW to Data Valid		22		25	ns
t _{LZOE}	OE LOW to Low Z [13]	5		5		ns
t _{HZOE}	OE HIGH to High Z [13, 14]		18		20	ns
t _{LZCE}	CE LOW to Low Z [13]	10		10		ns
t _{HZCE}	CE HIGH to High Z [13, 14]		18		20	ns
t _{PU}	CE LOW to Power Up	0		0		ns
t _{PD}	CE HIGH to Power Down		45		55	ns
t _{DBE}	BLE/BHE LOW to Data Valid		22		25	ns
t _{LZBE}	BLE/BHE LOW to Low Z [13]	5		5		ns
t _{HZBE}	BLE/BHE HIGH to High Z [13, 14]		18		20	ns
Write Cycle [1	5]					
t _{WC}	Write Cycle Time	45		55		ns
t _{SCE}	CE LOW to Write End	35		40		ns
t _{AW}	Address Setup to Write End	35		40		ns
t _{HA}	Address Hold from Write End	0		0		ns
t _{SA}	Address Setup to Write Start	0		0		ns
t _{PWE}	WE Pulse Width	35		40		ns
t _{BW}	BLE/BHE LOW to Write End	35		40		ns
t _{SD}	Data Setup to Write End			25		ns
t _{HD}	Data Hold From Write End	0		0		ns
t _{HZWE}	WE LOW to High Z [13, 14]		18		20	ns
t _{LZWE}	WE HIGH to Low Z [13]	10		10		ns

Notes

 ^{11.} Test conditions for all parameters other than tri-state parameters assume signal transition time of 3 ns (1V/ns) or less, timing reference levels of V_{CC(typ)}/2, input pulse levels of 0 to V_{CC(typ)}, and output loading of the specified lol lol lol as shown in the "AC Test Loads and Waveforms" on page 4.
 12. AC timing parameters are subject to byte enable signals (BHE or BLE) not switching when chip is disabled. Please see application note AN13842 for further clarification.

^{13.} At any given temperature and voltage condition, t_{HZCE} is less than t_{LZCE} , t_{HZDE} is less than t_{LZOE} , t_{HZOE} is less than t_{LZOE} , and t_{HZWE} is less than t_{LZWE} for any given

^{14.} t_{HZOE}, t_{HZCE}, t_{HZCE}, t_{HZCE}, and t_{HZWE} transitions are measured when the <u>outputs</u> enter <u>a high</u> impedance state.

15. The internal write time of the memory is defined by the overlap of WE, CE = V_{IL}, BHE and/or BLE = V_{IL}. All signals are ACTIVE to initiate a write and any of these signals can terminate a write by going INACTIVE. The data input setup and hold timing are referenced to the edge of the signal that terminates the write.



Switching Waveforms

Figure 5. Read Cycle No.1: Address Transition Controlled. [16, 17]

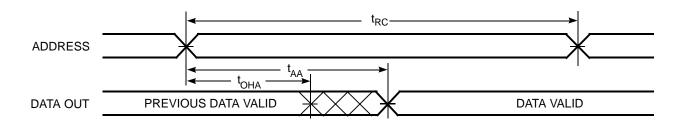
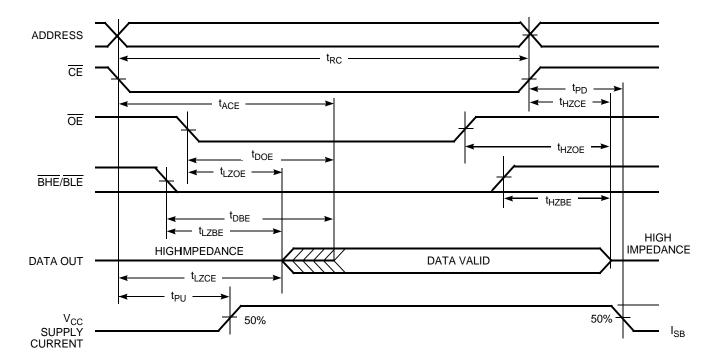


Figure 6. Read Cycle No. 2: $\overline{\text{OE}}$ Controlled [17, 18]



^{16.} The device is continuously selected. \overline{OE} , $\overline{CE} = V_{|L}$, \overline{BHE} and $\overline{BLE} = V_{|L}$.

17. \overline{WE} is HIGH for read cycle.

^{18.} Address valid before or similar to $\overline{\text{CE}}$ and $\overline{\text{BHE}}$, $\overline{\text{BLE}}$ transition LOW.



Switching Waveforms (continued)

Figure 7. Write Cycle No 1: WE Controlled [15, 19, 20]

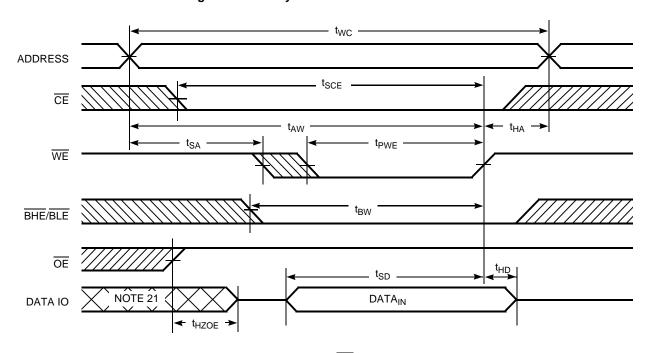
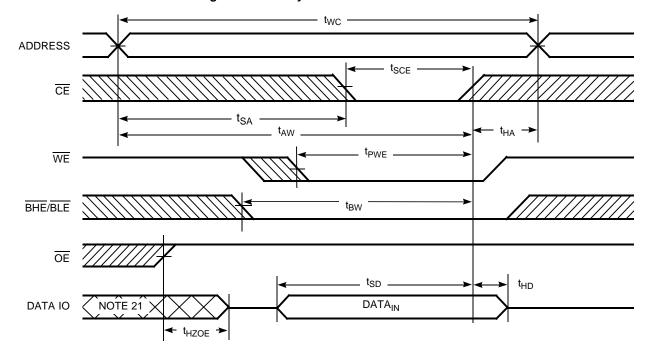


Figure 8. Write Cycle 2: CE Controlled [15, 19, 20]



- Notes
 19. Data IO is high impedance if $\overline{OE} = V_{IH}$.
 20. If \overline{CE} goes HIGH simultaneously with WE = V_{IH} , the output remains in a high impedance state.
 21. During this period, the IOs are in output state. Do not apply input signals.



Switching Waveforms (continued)

Figure 9. Write Cycle 3: WE controlled, OE LOW [20]

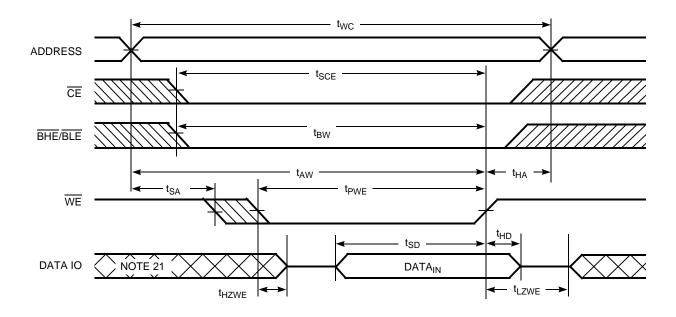
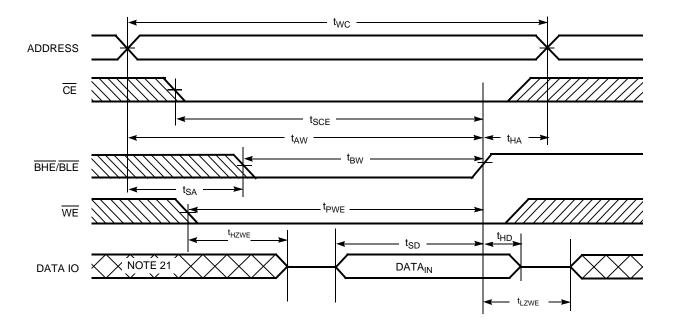


Figure 10. Write Cycle 4: BHE/BLE Controlled, OE LOW [20]





Truth Table

CE	WE	OE	BHE	BLE	Inputs or Outputs	Mode	Power
Н	Х	Х	Х	Х	High Z	Deselect or Power Down	Standby (I _{SB})
Х	Χ	Х	Н	Н	High Z	Deselect or Power Down	Standby (I _{SB})
L	Н	L	L	L	Data Out (IO ₀ –IO ₁₅)	Read	Active (I _{CC})
L	Н	L	Н	L	Data Out (IO ₀ –IO ₇); IO ₈ –IO ₁₅ in High Z	Read	Active (I _{CC})
L	Н	L	L	Н	Data Out (IO ₈ –IO ₁₅); IO ₀ –IO ₇ in High Z	Read	Active (I _{CC})
L	Н	Н	L	L	High Z	Output Disabled	Active (I _{CC})
L	Н	Н	Н	L	High Z	Output Disabled	Active (I _{CC})
L	Н	Н	L	Н	High Z	Output Disabled	Active (I _{CC})
L	L	Х	L	L	Data In (IO ₀ –IO ₁₅)	Write	Active (I _{CC})
L	L	Х	Н	L	Data In (IO ₀ –IO ₇); IO ₈ –IO ₁₅ in High Z	Write	Active (I _{CC})
L	L	Х	L	Н	Data In (IO ₈ –IO ₁₅); IO ₀ –IO ₇ in High Z	Write	Active (I _{CC})



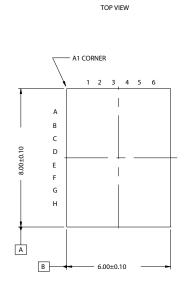
Ordering Information

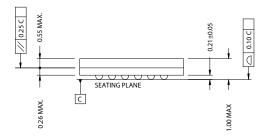
Speed (ns)	Ordering Code	Package Diagram	Package Type	Operating Range
45	CY62136FV30LL-45BVXI	51-85150	48-Ball VFBGA (Pb-Free)	Industrial
	CY62136FV30LL-45ZSXI	51-85087	44-Pin TSOP II (Pb-Free)	
	CY62136FV30LL-45ZSXA	51-85087	44-Pin TSOP II (Pb-Free)	Automotive-A
55	CY62136FV30LL-55ZSXE	51-85087	44-Pin TSOP II (Pb-Free)	Automotive-E

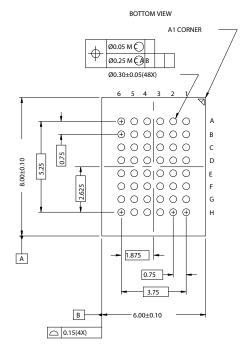
Contact your local Cypress sales representative for availability of these parts.

Package Diagrams

Figure 11. 48-Ball VFBGA (6 x 8 x 1 mm)







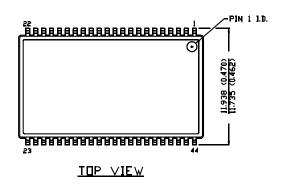
51-85150-*D

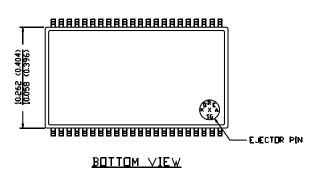


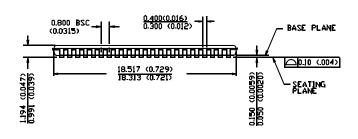
Package Diagrams (continued)

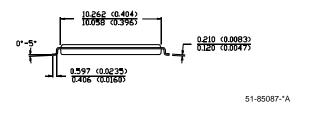
Figure 12. 44-Pin TSOP II

D[MENS|DN [N MM ([NCH) MAX MIN.











Document History Page

		Y62136FV30 er: 001-08402	MoBL [®] 2-Mb	it (128K x 16) Static RAM
Rev.	ECN No.	Submission Date	Orig. of Change	Description of Change
**	467351	See ECN	NXR	New datasheet
*A	797956	See ECN	VKN	Converted from preliminary to final Changed $I_{SB1(typ)}$ and $I_{SB1(max)}$ specification from 0.5 μ A to 1.0 μ A and 2.5 μ A to 5.0 μ A, respectively Changed $I_{SB2(typ)}$ and $I_{SB2(max)}$ specification from 0.5 μ A to 1.0 μ A and 2.5 μ A to 5.0 μ A, respectively Changed $I_{CCDR(typ)}$ and $I_{CCDR(max)}$ specification from 0.5 μ A to 1.0 μ A and 2.5 μ A to 4.0 μ A, respectively Changed $I_{CC(max)}$ specification from 2.25 μ A to 2.5 μ A
*B	869500	See ECN	VKN	Added Automotive information Updated Ordering information table Added footnote 12 related to t _{ACE}
*C	901800	See ECN	VKN	Added footnote 9 related to I _{SB2} and I _{CCDR} Made footnote 13 applicable to AC parameters from t _{ACE}
*D	1371124	See ECN	VKN/AESA	Converted Automotive information from preliminary to final Changed I_{IX} min spec from $-1~\mu\text{A}$ to $-4~\mu\text{A}$ and I_{IX} max spec from $+1~\mu\text{A}$ to $+4~\mu\text{A}$ Changed I_{OZ} min spec from $-1~\mu\text{A}$ to $-4~\mu\text{A}$ and I_{OZ} max spec from $+1~\mu\text{A}$ to $+4~\mu\text{A}$ Changed I_{DBE} spec from 55 ns to 25 ns for automotive part
*E	2594937	10/22/08	NXR/PYRS	Added Automotive-A information Changed t _{LZBE} from 10 ns to 5 ns for -55.

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